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	772 1	Search Text	DB	Time stamp
L Number	1288		USPAT	2002/11/15 13:11
1			USPAT	2002/11/15 13:12
2	589379	silicon naer2 nitirde	USPAT	2002/11/15 13:12
3	288635	(silicon naer2 nitirde) and (silicon naer2	USPAT	2002/11/15 13:12
4	927	(silicon naerz nitirde) and (silicon naerz	• • • • • • • • • • • • • • • • • • • •	
		oxide) and ellipsometry	USPAT	2002/11/15 13:12
5	1137	ellipsometry and thickness	USPAT	2002/11/15 13:12
6	1137	(ellipsometry and thickness) and thickness		2002/11/15 13:13
7	860	((silicon naer2 nitirde) and (silicon	USPAT	2002/11/13 13:13
,		naer2 oxide) and ellipsometry) and		
		thickness		
	789	(((silicon naer2 nitirde) and (silicon	USPAT	2002/11/15 13:13
9	,65	naer2 oxide) and ellipsometry) and		
		thickness) and time		
	670	((((silicon naer2 nitirde) and (silicon	USPAT	2002/11/15 13:15
10	672	((((SIIICON MACEZ MICHAE) and		
		naer2 oxide) and ellipsometry) and		
		thickness) and time) and (wafer		
		semiconductor)	rro Dam	2002/11/15 13:16
11	410	(((((silicon naer2 nitirde) and (silicon	USPAT	2002/11/13 13:10
		naer2 oxide) and ellipsometry) and	l	
		thickness) and time) and (wafer		
1		semiconductor)) and (etch\$3 engrav\$3)		
12	26	l o !!!!! l/ilioon	USPAT	2002/11/15 13:18
12	20	naer2 oxide) and ellipsometry) and	[
1		thickness) and time) and (wafer	1	
		semiconductor)) and (etch\$3 engrav\$3)) and		i
		semiconductor)) and (etchips englaves), and		
		(optical near5 emission)	USPAT	2002/11/15 13:19
13	21	(((((((silicon naer2 nitirde) and (silicon	USERI	2002/11/10 10:11
		naer2 oxide) and ellipsometry) and		
		thickness) and time) and (wafer		
ì		semiconductor)) and (etch\$3 engrav\$3)) and		
1		(optical near5 emission)) and ((measur\$3		1
		determin\$3) near5 thickness)		
	51948	measur\$3 near20 thickness	USPAT;	2002/10/30 13:49
] -	31940	measurys nearzy emzemies	US-PGPUB	
	0500	(measur\$3 near20 thickness) and (etch\$3	USPAT;	2002/10/30 13:50
-	9538		US-PGPUB	
		engrav\$3)	USPAT;	2002/10/30 13:53
-	6466	((measur\$3 near20 thickness) and (etch\$3	US-PGPUB	2002, 20, 00
		engrav\$3)) and (dielectric insulat\$3	02-16100	
		(silicon near3 nitride) (silicon near3		
		oxide) ("Si.sub.3" adj2 "N.sub.4") ("Si"		
		adj2 "O.sub.2"))		
1_	4021	(((measur\$3 near20 thickness) and (etch\$3	USPAT;	2002/10/30 13:55
		engrav\$3)) and (dielectric insulat\$3	US-PGPUB	
		(silicon near3 nitride) (silicon near3		
		oxide) ("Si.sub.3" adj2 "N.sub.4") ("Si"		
		adj2 "O.sub.2"))) and (optical emission		
		aujz O.Sub.z /// and (opered emission	1	
		spectrum distribution)	USPAT;	2002/10/30 13:56
-	622	((((measur\$3 near20 thickness) and (etch\$3	US-PGPUB	
		engrav\$3)) and (dielectric insulat\$3	US-FGFUD	
		(silicon near3 nitride) (silicon near3		
		oxide) ("Si.sub.3" adj2 "N.sub.4") ("Si"		
		adi2 "O.sub.2"))) and (optical emission		
i	1	spectrum distribution)) and amplitude		
_	587	((((measur\$3 near20 thickness) and	USPAT;	2002/10/30 13:56
		(etch\$3 engrav\$3)) and (dielectric	US-PGPUB	
		insulat\$3 (silicon near3 nitride) (silicon		1
	1	near3 oxide) ("Si.sub.3" adj2 "N.sub.4")		
		("Si" adj2 "O.sub.2"))) and (optical		
		(of auja 0.5ub.2 /// and (optical		ì
		emission spectrum distribution)) and		
		amplitude) and time	HCDATT.	2002/10/30 13:57
-	566	((((((measur\$3 near20 thickness) and	USPAT;	2002/10/30 13.5/
		(etch\$3 engrav\$3)) and (dielectric	US-PGPUB	
		insulat\$3 (silicon near3 nitride) (silicon		
		near3 oxide) ("Si.sub.3" adj2 "N.sub.4")		
		("Si" adj2 "O.sub.2"))) and (optical		
		emission spectrum distribution)) and		
1		amplitude) and time) and (semiconductor		
		wafer substrate)		
1	1	MOTET SUDSCIOCE!		

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Ś	45)

			W0237	2002/10/31 10:35
	475	(((((measur\$3 near20 thickness) and	USPAT '	2002/10/31 10.33
-	1,3	(otch\$3 engray\$3)) and (dielectric		
		inculated (silicon near3 nitride) (silicon		
	1	near3 oxide) ("Si.sub.3" adj2 "N.sub.4")		
		("Si" adj2 "O.sub.2"))) and (optical		1
		emission spectrum distribution)) and		1
		emission spectrum distribution// and		ľ
		amplitude) and time) and (semiconductor		
		wafer substrate)	US-PGPUB;	2002/10/31 10:13
_	91	(((((measur\$3 near20 thickness) and		2002/10/01
		(etch\$3 engrav\$3)) and (dielectric	EPO	
		insulat\$3 (silicon near3 nitride) (silicon		1
		near3 oxide) ("Si.sub.3" adj2 "N.sub.4")		
		("Si" adi2 "O.sub.2"))) and (optical		
		emission spectrum distribution)) and		
		amplitude) and time) and (semiconductor		
		wafer substrate)		
	0.0	(((((measur\$3 near20 thickness) and	US-PGPUB;	2002/10/31 10:13
-	92	(etch\$3 engrav\$3)) and (dielectric	EPO	
		insulat\$3 (silicon near3 nitride) (silicon	-	
		insulated (Silicon Heard Hittide) (Silicon		
		near3 oxide) ("Si.sub.3" adj2 "N.sub.4")		
		("Si" adj2 "O.sub.2"))) and (optical		
		emission spectrum distribution)) and		
		amplitude) and time) and (semiconductor		
		wafer substrate)		2002/10/31 11:16
_	1157	(((((((measur\$3 determin\$5) near20	USPAT	2002/10/31 11:10
		thickness) and (etch\$3 polish\$3 engrav\$3))		
		and (dielectric insulat\$3 (silicon near3		
		nitride) (silicon near3 oxide) ("Si.sub.3"		·
İ		adj2 "N.sub.4") ("Si" adj2 "O.sub.2")))		
		and (optical emission spectrum		
		distribution)) and amplitude) and time)		
		and (semiconductor wafer substrate)		
		e2prom eeprom eprom) (flash near5 memory	USPAT	2002/10/31 10:55
_	42035	ezprom eeprom eprom) (IIash hears memory)	USPAT	2002/10/31 10:57
-	39	(e2prom eeprom eprom) (flash near5 memory)	OSIMI	2002, 20, 3
		and ((((((measur\$3 determin\$5) near20		
1		thickness) and (etch\$3 polish\$3 engrav\$3))		
		and (dielectric insulat\$3 (silicon near3		
		nitride) (silicon near3 oxide) ("Si.sub.3"		
		adj2 "N.sub.4") ("Si" adj2 "O.sub.2")))		
		and (optical emission spectrum		
1		distribution)) and amplitude) and time)		
_	1	((((((measur\$3 determin\$5) near20	EPO; JPO;	2002/10/31 11:29
_	1	thickness) and (etch\$3 polish\$3 engrav\$3))	DERWENT;	
		and (dielectric insulat\$3 (silicon near3	IBM TDB	
	1	nitride) (silicon near3 oxide) ("Si.sub.3"	_	
		adj2 "N.sub.4") ("Si" adj2 "O.sub.2")))		
		aujz N.Sub.4 / (or aujz 0.5ub.2 ///		
		and (optical emission spectrum		
		distribution)) and amplitude) and time)		
		and (semiconductor wafer substrate)	USPAT	2002/10/31 11:32
-] 3	thickness same measur\$3 same time same	OSENI	1 2002/20/01 11:02
		etch\$3 same emission same spectrum	HCDAM	2002/10/31 11:33
-	1973		USPAT	2002/10/31 11.33
		and emission and spectrum		2002/10/21 11:34
_	204	(thickness and measur\$3 and time and	USPAT	2002/10/31 11:34
		etch\$3 and emission and spectrum) and (ONO	1	
		(oxide near5 nitride near5 oxide))		
		1 1 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2		